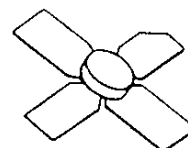


RF & MICROWAVE TRANSISTORS VHF PORTABLE/MOBILE APPLICATIONS

- 150 MHz
- 7.5 VOLTS
- COMMON EMITTER
- $P_{OUT} = 2.5 \text{ W MIN. WITH } 11.0 \text{ dB GAIN}$

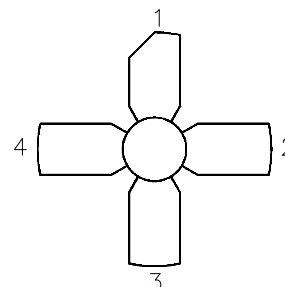


.280 4LSL (M123)
epoxy sealed

ORDER CODE
SD1135-03

BRANDING
1135-3

PIN CONNECTION



1. Collector	3. Base
2. Emitter	4. Emitter

DESCRIPTION

The SD1135-03 is a 7.5 V Class C epitaxial silicon NPN planar transistor designed primarily for VHF communications. It withstands severe mismatch under operating conditions.

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}\text{C}$)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	36	V
V_{CER}	Collector-Emitter Voltage	16	V
V_{CES}	Collector-Emitter Voltage	36	V
V_{EBO}	Emitter-Base Voltage	4.0	V
I_C	Device Current	1.7	A
P_{DISS}	Power Dissipation	15	W
T_J	Junction Temperature	+200	$^{\circ}\text{C}$
T_{STG}	Storage Temperature	- 65 to +150	$^{\circ}\text{C}$

THERMAL DATA

$R_{TH(j-c)}$	Junction-Case Thermal Resistance	11.6	$^{\circ}\text{C/W}$
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ELECTRICAL SPECIFICATIONS ($T_{\text{case}} = 25^{\circ}\text{C}$)**STATIC**

Symbol	Test Conditions	Value			Unit
		Min.	Typ.	Max.	
BV_{CES}	$I_{\text{C}} = 10\text{mA}$ $V_{\text{BE}} = 0\text{V}$	36	—	—	V
BV_{CEO}	$I_{\text{C}} = 50\text{mA}$ $I_{\text{B}} = 0\text{mA}$	16	—	—	V
BV_{EBO}	$I_{\text{E}} = 2\text{mA}$ $I_{\text{C}} = 0\text{mA}$	4.0	—	—	V
I_{CER}	$V_{\text{CE}} = 10\text{V}$ $R_{\text{BE}} = 50\Omega$	—	—	0.5	mA
I_{CBO}	$V_{\text{CB}} = 15\text{V}$ $I_{\text{E}} = 0\text{mA}$	—	—	1.0	mA
h_{FE}	$V_{\text{CE}} = 5\text{V}$ $I_{\text{C}} = 200\text{mA}$	20	—	—	—

DYNAMIC

Symbol	Test Conditions	Value			Unit
		Min.	Typ.	Max.	
P_{OUT}	$f = 150\text{ MHz}$ $V_{\text{CC}} = 7.5\text{ V}$	2.5	—	—	W
G_{P}	$f = 150\text{ MHz}$ $V_{\text{CC}} = 7.5\text{ V}$	11.0	—	—	dB
C_{OB}	$f = 1\text{ MHz}$ $V_{\text{CB}} = 7.5\text{ V}$	—	19	—	pF

IMPEDANCE DATA

TYPICAL INPUT IMPEDANCE

FREQ.	$Z_{\text{IN}} (\Omega)$	$Z_{\text{CL}} (\Omega)$
150 MHz	$2.2 - j 0.4$	$7.9 + j 8.4$
160 MHz	$1.9 - j 0.8$	$7.6 + j 8.2$
170 MHz	$1.0 - j 1.0$	$6.0 + j 8.3$

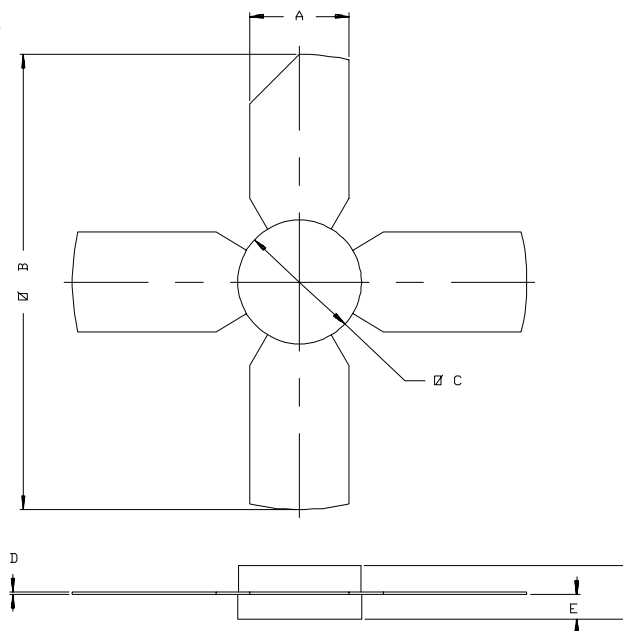
TYPICAL COLLECTOR LOAD IMPEDANCE

$$P_{\text{OUT}} = 2.5\text{W}$$

$$V_{\text{CE}} = 7.5\text{V}$$

PACKAGE MECHANICAL DATA

Ref.: Dwg. No.12-0123



SGS-THOMSON MICROELECTRONICS		
	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	.220/5,59	.230/5,84
B	-----	1.055/26,8
C	.275/6,99	.285/7,24
D	.004/0,10	.006/0,15
E	.050/1,27	.060/1,52
F	.118/3,00	.130/3,30

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